SILICON (Si) POWER MOSFET ▲ CEM2152



CEM2152

20V ▲ 16mΩ ▲ 9A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} With ESD diode between Gate and Source





RoHS

REACH

MAXIMUM RATINGS

Parameter ($T_A = 25^{\circ}C$, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	20V
Gate-Source Voltage	V _{GS}	±12V
Continuous Drain Current	Ι _D	9A
Pulsed Drain Current Note 1	I _{DM}	36A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

Battery	DC	Load	Power	USB
Pack	Fan	Switches	Banks	Storage
+ 4 -			4	Ŷ

PIN DESCRIPTION

Circuit Diagram	Outline • Top View	Pin No.	Description
G (4)		1 2 3 4 5	Source Source Gate Drain
S (1,2,3)		6 7 8	Drain Drain Drain

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV _{DSS}	20			V
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 12V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -12V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	0.4		1	V
Static Drain-Source On-Resistance	$V_{GS} = 4.5V, I_{D} = 6A$	R _{DS(ON)}		16	20	mΩ
Static Drain-Source On-Resistance	V_{GS} = 2.5V, I_{D} = 5.2A	R _{DS(ON)}		20	26	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{ISS}		555		рF
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	Coss		100		рF
Reverse Transfer Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{RSS}		75		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 6A, $R_{G(ext)}$ = 6 Ω	t _{D(ON)}		10		ns
Turn-On Rise Time	V_{DD} = 16V, V_{GS} = 4.5V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _R		14		ns
Turn-Off Delay Time	V_{DD} = 16V, V_{GS} = 4.5V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _{D(OFF)}		37		ns
Turn-Off Fall Time	V_{DD} = 16V, V_{GS} = 4.5V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _F		9		ns
Total Gate Charge	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 6A	Q_{G}		11		nC
Gate Source Charge	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 6A	Q _{GS}		2		nC
Gate Drain Charge	V_{DD} = 16V, V_{GS} = 4.5V, I_{D} = 6A	\mathbf{Q}_{GD}		3		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note 2}		١ _s			2	А
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V$, $I_S = 2A$	V_{SD}			1.2	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, $t \le 10$ sec

3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

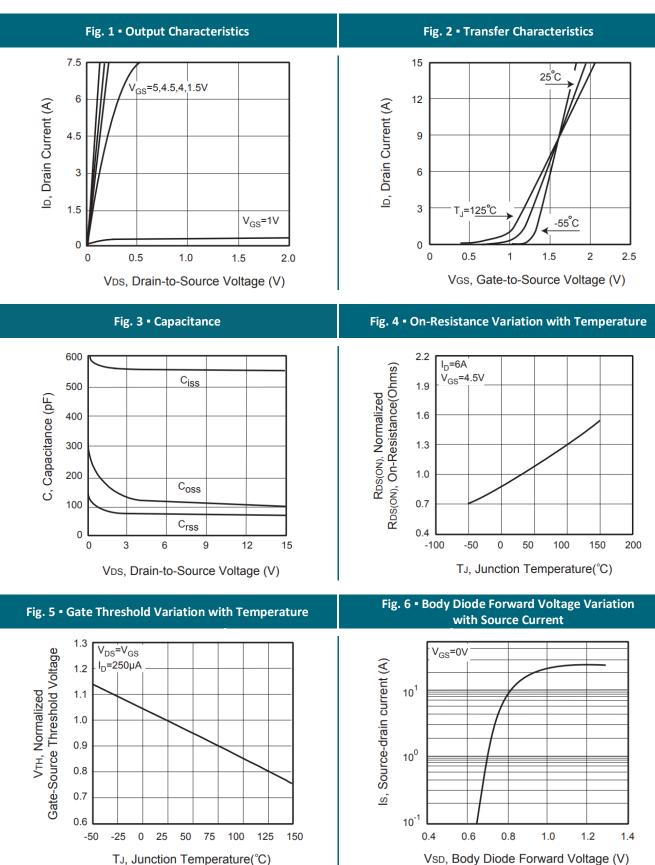
4: Guaranteed by design, not subject to production testing.



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

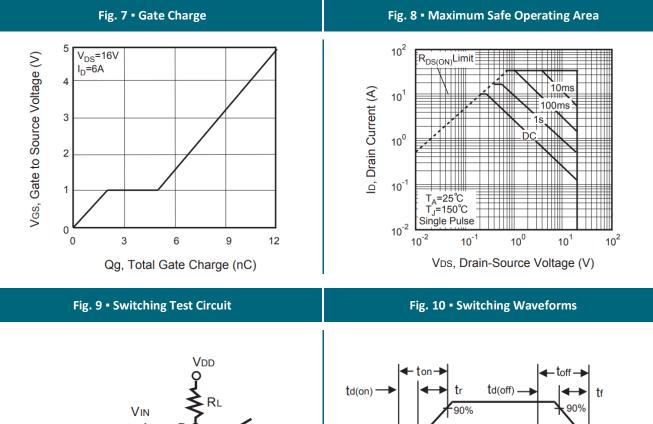


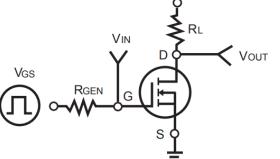
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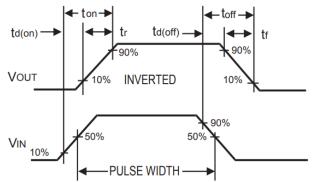


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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE







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REFERENCE DATA ▲TYPICAL DEVICE PERFORMANCE

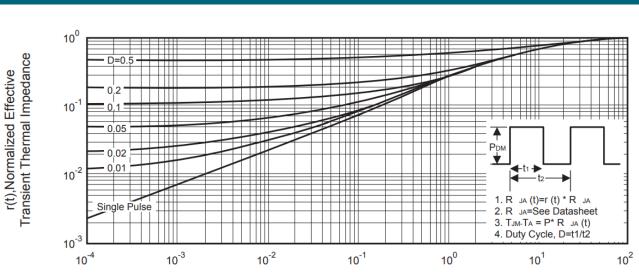
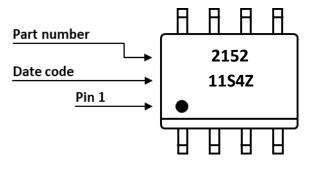


Fig. 11 • Normalized Thermal Transient Impedance Curve

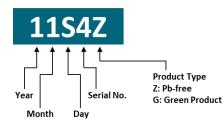
Square Wave Pulse Duration (sec)

PART MARKING



DATE CODE

Example: 11S4Z



Coding list for "Day"										
1	2	3	4	5	6	7	8	9	Α	
01	02	03	04	05	06	07	08	09	10	
В	С	D	Ε	F	G	Н	I	J	K	
11	12	13	14	15	16	17	18	19	20	
L	Μ	Ν	0	Ρ	Q	R	S	Т	U	
21	22	23	24	25	26	27	28	29	30	
v										
31										

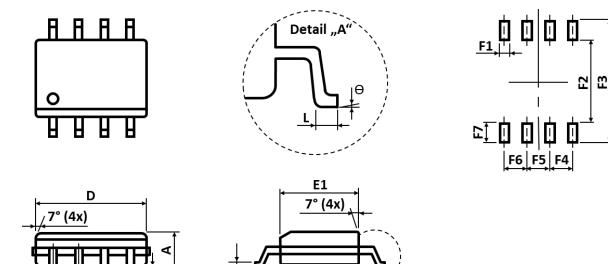
Coding list for "Month"



• Detail "A"



PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)	
А	1.350	-	1.750	E1	3.700		4.060	
A1	0.100	-	0.250	eB	5.800		6.200	
В	0.310	-	0.510	е		1.270		
С	0.170	-	0.250	L	0.400		0.950	
D	4.690	-	5.000	θ	0°	-	8°	
Course.	Millimeters	Millimeters	Millimeters	C. une	Millimeters	Millimeters	Millimeters	

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
54		0 5 0 0				4 270	
F1	-	0.500	-	F5	-	1.270	-
F2	-	4.250	-	F6	-	1.270	-
F3	-	6.250	-	F7	-	1.000	-
F4	-	1.270	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

ORDERING INFORMATION

В

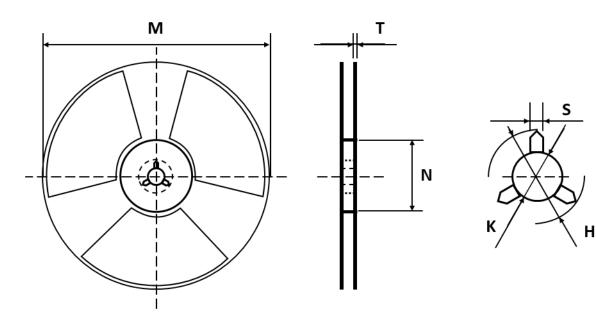
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEM2152	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs	



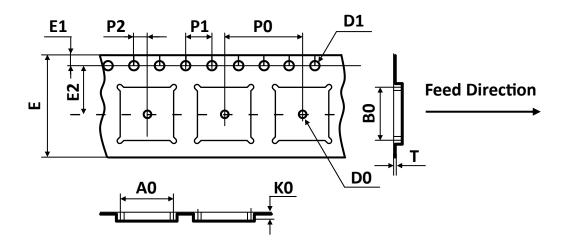


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	9550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS All dimensions in mm



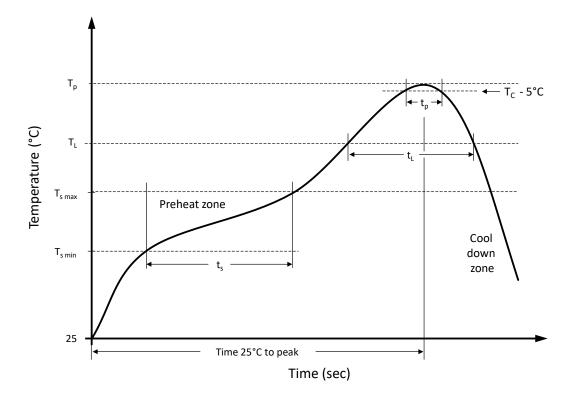
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
509	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
SO8	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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